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RoHS Declaration of Conformity

Unipower LLC Part Number	Description
XPGE12.48G	Aspiro Rectifier 1200W, 48V
Models may be followed by G, SXXX, or SXXXG where "X" are alphanumeric characters, indicating non-safety critical options and does not impact the RoHS Declaration stated herein.	

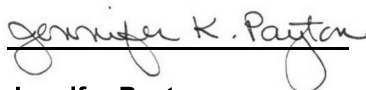
This is to certify that we, Unipower LLC, hereby declare that the product(s) listed above is(are) in full compliance with EU Directive 2011/65/EU and EU Directive 2015/863 of the European Parliament and the Council for restricting the application of hazardous substances in electric and electronic devices. Unipower LLC has identified the product(s) listed as RoHS compliant and has a maximum concentration by weight in homogeneous materials as defined in Annex II of EU Directive 2011/65/EU and EU Directive 2015/863 or qualify for an exemption as indicated.

Restricted Substance	Maximum Concentration Values Tolerated by Weight in Homogeneous Materials
Lead	0.1%
Mercury	0.1%
Cadmium	0.01%
Hexavalent Chromium	0.1%
Polybrominated Biphenyls (PBB)	0.1%
Polybrominated Diphenyl Ethers (PBDE)	0.1%
Bis(2-Ethylhexyl) Phthalate (DEHP)	0.1%
Benzyl Butyl Phthalate (BBP)	0.1%
Dibutyl Phthalate (DBP)	0.1%
Diisobutyl Phthalate (DIBP)	0.1%

Declared Exemptions:

- 6(C) – Copper Alloy containing up to 4% lead by weight
- 7(A) - Lead in high melting temperature type solders (i.e. lead- based alloys containing 85 % by weight or more lead)
- 7(C)-I - Electrical and electronic components containing lead in a glass or ceramic other than dielectric ceramic in capacitors, e.g. piezoelectronic devices, or in a glass or ceramic matrix compound
- 7(C)-II - Lead in dielectric ceramic in capacitors for a rated voltage of 125 V AC or 250 V DC or higher
- 15(A) - Lead in solders to complete a viable electrical connection between the semiconductor die and carrier within integrated circuit flip chip packages where at least one of the following criteria applies:
 - a semiconductor technology node of 90 nm or larger
 - a single die of 300 mm² or larger in any semiconductor technology node;
 - stacked die packages with die of 300 mm² or larger, or silicon interposers of 300 mm² or larger.

Authorized Signatory For Unipower LLC:



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